



# N 沟道增强型场效应晶体管

## N-CHANNEL MOSFET

### FHP150N03C

#### 主要参数 MAIN CHARACTERISTICS

ID	150 A
VDSS	26 V
Rdson-typ ( @Vgs=10V)	2.2mΩ
Rdson-typ ( @Vgs=4.5V)	2.8mΩ
Qg-typ	85nC

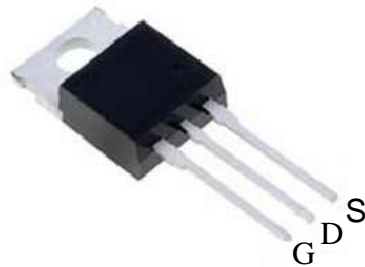
#### 产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 405pF)	Low Crss (typical 405pF)
开关速度快	Fast switching
100%经过雪崩测试	100% avalanche tested
高抗 dv/dt 能力	Improved dv/dt capability
RoHS 产品	RoHS product

#### 用途 APPLICATIONS

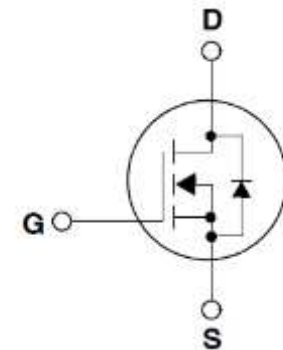
电池管理系统	BMS
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#### 封装形式 Package



TO-220  
FHP series

#### 等效电路 Equivalent Circuit



#### 绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
		FHP150N03C	
最高漏极-源极直流电压 Drain-Source Voltage	VDS	26	V
连续漏极电流* Drain Current -continuous *	ID (Tc=25°C)	150	A
	ID (Tc=100°C)	96	A
最大脉冲漏极电流 (注 1) Drain Current - pulse (note 1)	IDM	500	A
最高栅源电压 Gate-Source Voltage	VGS	±25	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	EAS	80	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	IAR	85	A
重复雪崩能量 (注 1) Repetitive Avalanche Current (note 1)	EAR	20	mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0	V/ns
耗散功率 Power Dissipation	PD (TC=25°C)	125	W
	-Derate above 25°C	1.33	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	TJ, TSTG	-55~+175	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	TL	300	°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature

## 电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 <b>Off –Characteristics</b>						
漏-源击穿电压 Drain-Source Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	26	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> =250μA, referenced to 25°C	-	0.03	-	V/°C
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, T <sub>C</sub> =25°C	-	-	1	μA
		V <sub>DS</sub> =20V, T <sub>C</sub> =125°C	-	-	100	μA
栅极体漏电流 Gate-body leakage current	I <sub>GSS</sub> (F/R)	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
通态特性 <b>On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.9	3.0	V
静态导通电阻 Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V , I <sub>D</sub> =40A	-	2.2	4	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =30A	-	3	6.5	
正向跨导 Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 20V, I <sub>D</sub> =40A (note 4)	-	90	-	S
动态特性 <b>Dynamic Characteristics</b>						
栅电阻 Gate Resistance	R <sub>g</sub>	f=1.0MHz, V <sub>DS</sub> OPEN	-	1.5	-	Ω
输入电容 Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz	-	5150	-	pF
输出电容 Output capacitance	C <sub>oss</sub>		-	580	-	
反向传输电容 Reverse transfer capacitance	C <sub>rss</sub>		-	405	-	
开关特性 <b>Switching Characteristics</b>						
延迟时间 Turn-On delay time	t <sub>d(on)</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =20A, R <sub>G</sub> =3Ω V <sub>GS</sub> =10V (note 4, 5)	-	14	-	ns
上升时间 Turn-On rise time	t <sub>r</sub>		-	18	-	ns
延迟时间 Turn-Off delay time	t <sub>d(off)</sub>		-	43	-	ns
下降时间 Turn-Off Fall time	t <sub>f</sub>		-	16	-	ns
栅极电荷总量 Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V , I <sub>D</sub> =20A , V <sub>GS</sub> =10V (note 4, 5)	-	85	-	nC
栅-源电荷 Gate-Source charge	Q <sub>gs</sub>		-	14	-	nC
栅-漏电荷 Gate-Drain charge	Q <sub>gd</sub>		-	23	-	nC
漏-源二极管特性及最大额定值 <b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current		I <sub>S</sub>	-	-	150	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I <sub>SM</sub>	-	-	500	A
正向压降 Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =40A	-	0.82	1.3	V
反向恢复时间 Reverse recovery time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A ,dI <sub>F</sub> /dt=100A/μs (note 4)	-	25	-	ns
反向恢复电荷 Reverse recovery charge	Q <sub>rr</sub>		-	23	-	nC

## 热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	最大值 Max	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	1.2	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	50	°C/W

注释:

- 1: 脉冲宽度由最高结温限制
- 2: L=0.1mH, IAS=40A, VDD=25V, RG=25 Ω, 起始结温 TJ=25°C
- 3: ISD ≤150A, di/dt ≤300A/μs, VDD≤BVDS, 起始结温 TJ=25°C
- 4: 脉冲测试: 脉冲宽度 ≤300μs, 占空比≤2%
- 5: 基本与工作温度无关

Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: L=0.1mH, IAS=40A, VDD=25V, RG=25 Ω, Starting TJ=25°C
- 3: ISD ≤150A, di/dt ≤300A/μs, VDD≤BVDS, Starting TJ=25°C
- 4: Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%
- 5: Essentially independent of operating temperatur

## Typical Characteristics

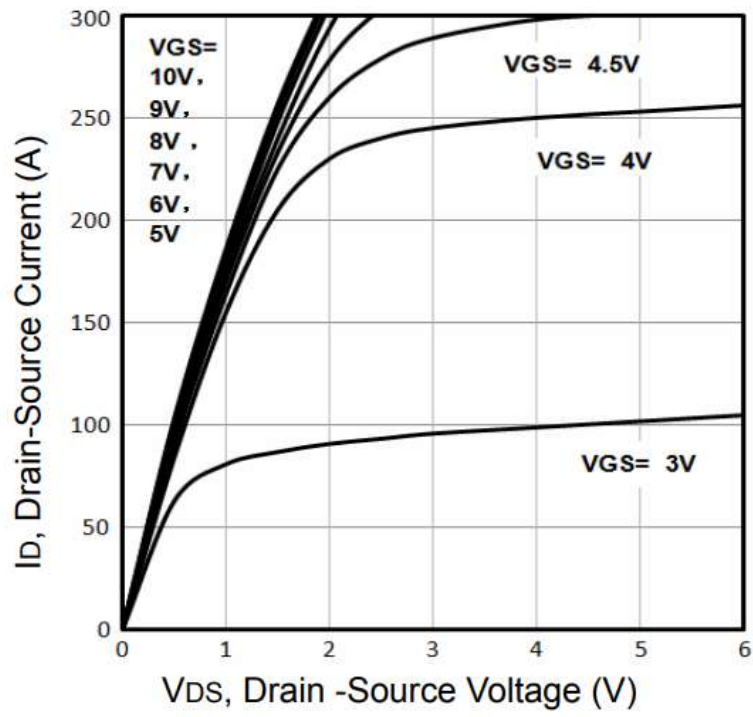


Fig1. Typical Output Characteristics

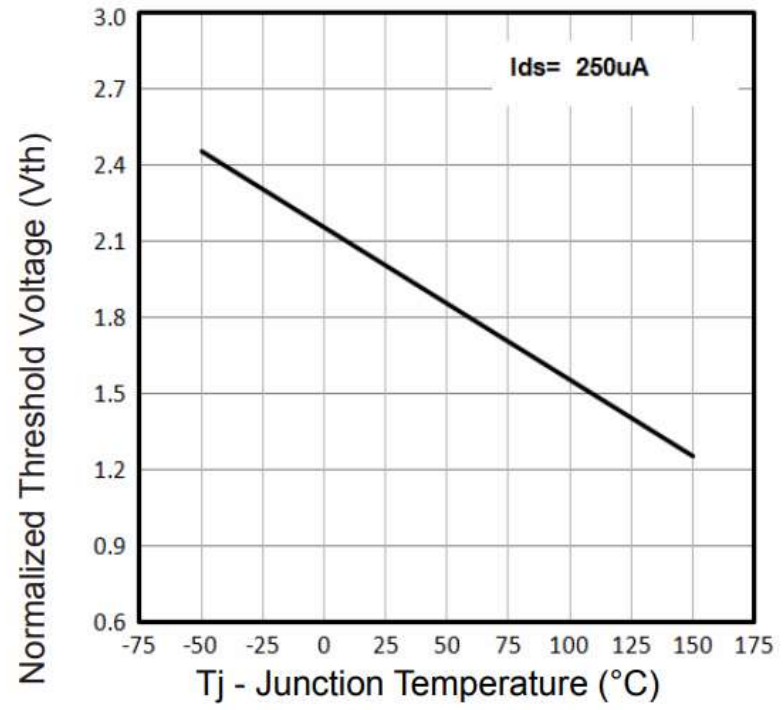


Fig2. Normalized Threshold Voltage Vs. Temperature

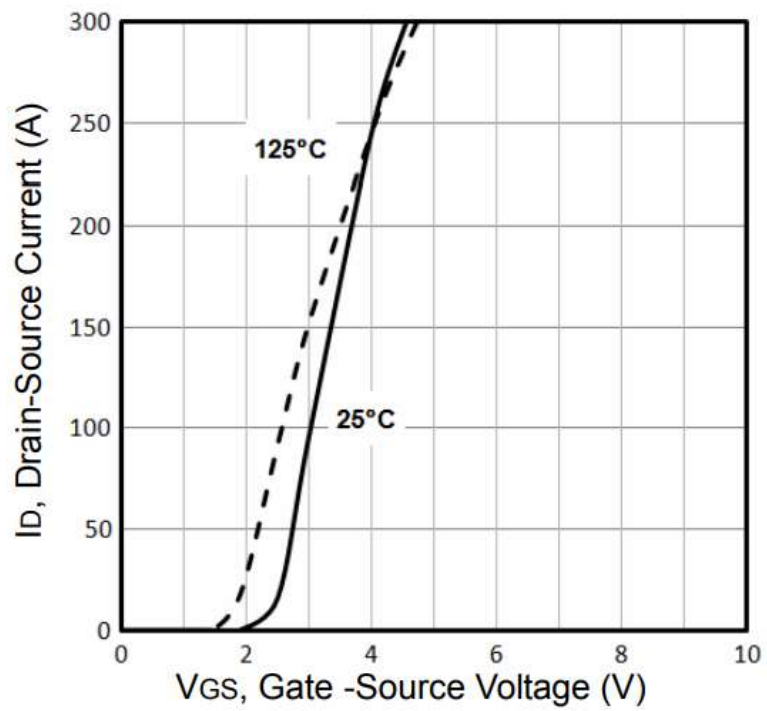


Fig3. Typical Transfer Characteristics

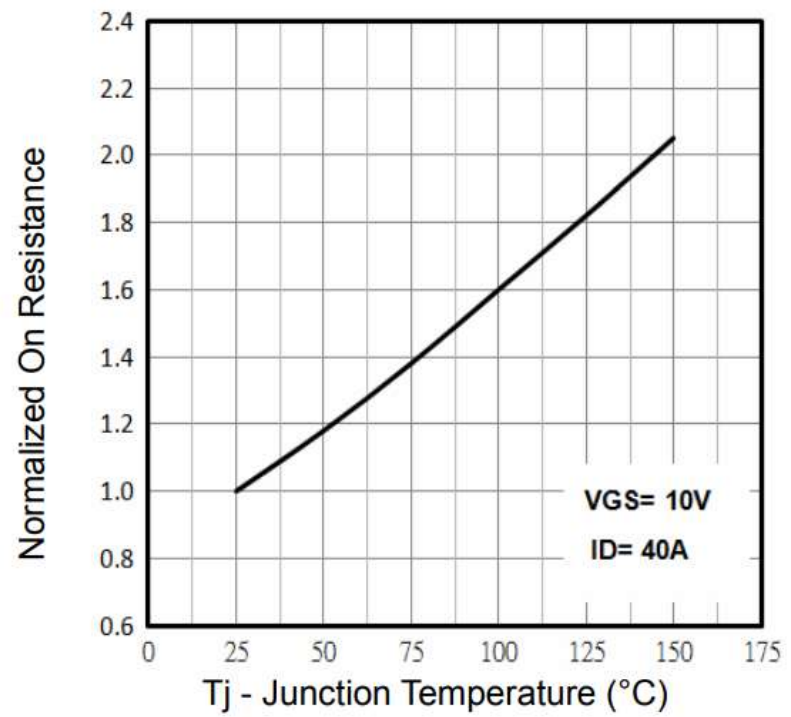


Fig4. Normalized On-Resistance Vs. Temperature

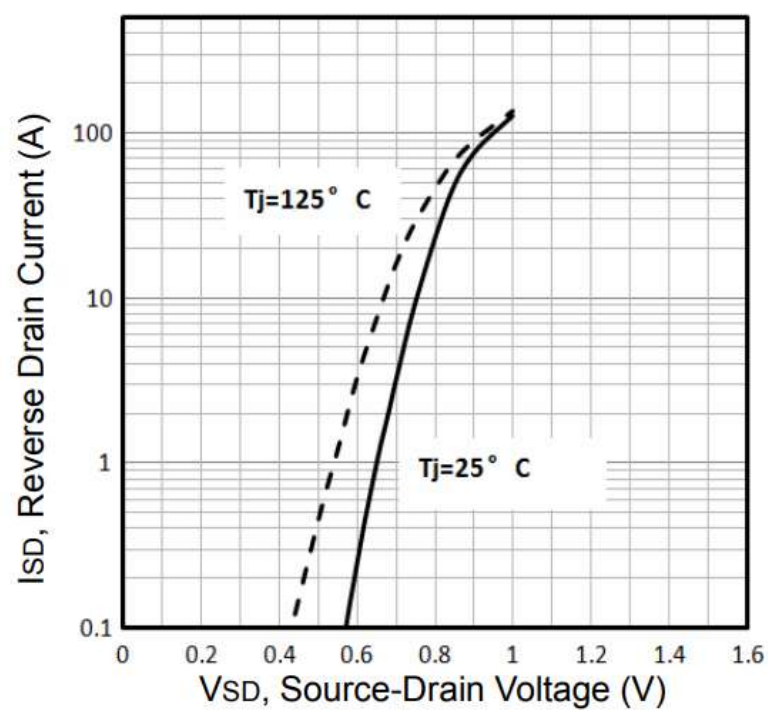


Fig5. Typical Source-Drain Diode Forward Voltage

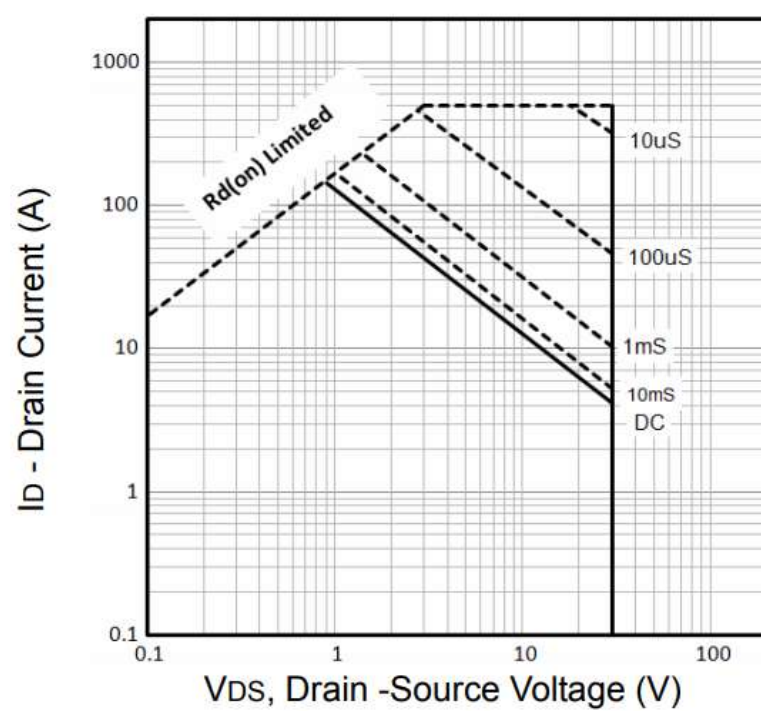


Fig6. Maximum Safe Operating Area

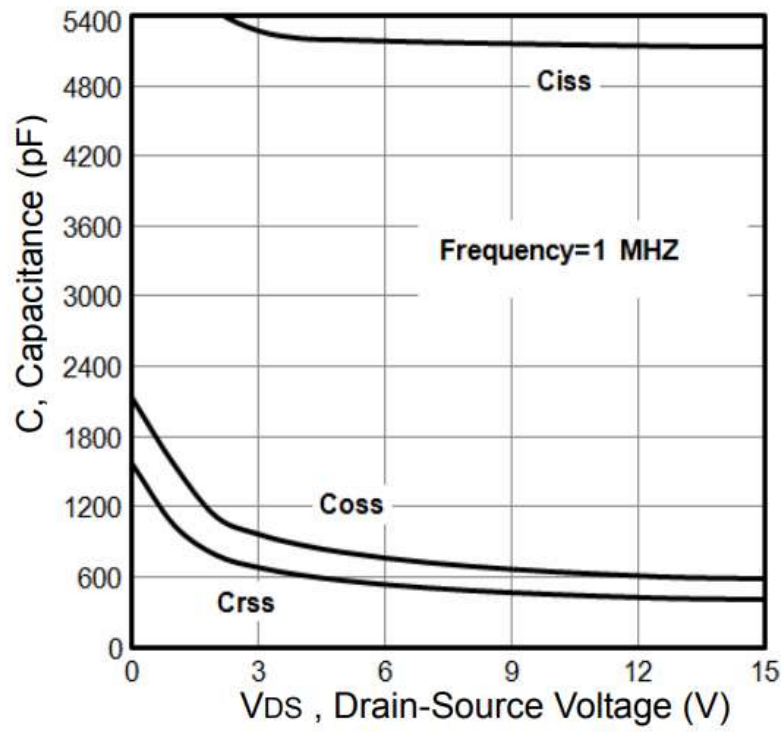


Fig7. Typical Capacitance Vs.Drain-Source Voltage

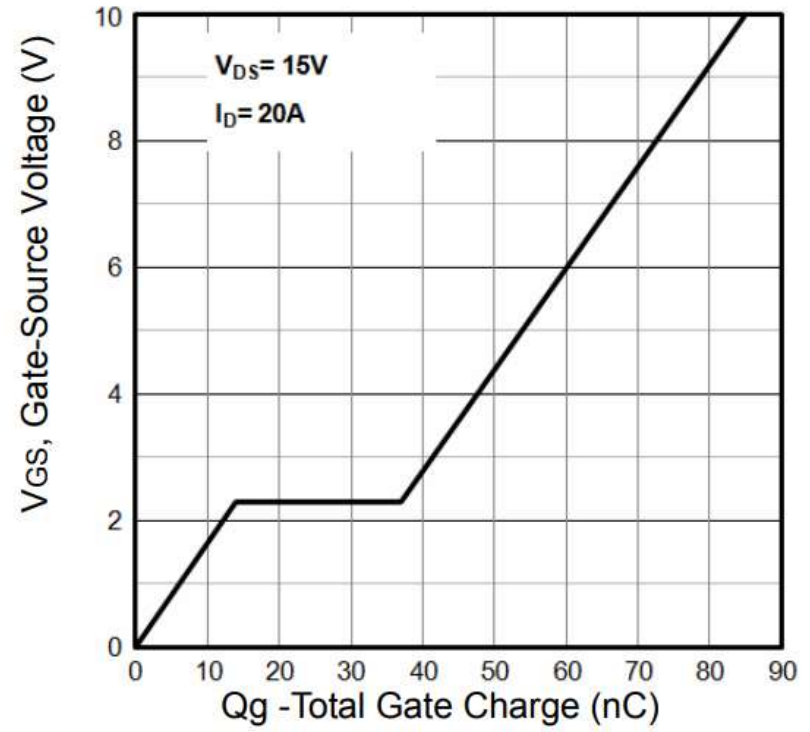


Fig8. Typical Gate Charge Vs.Gate-Source

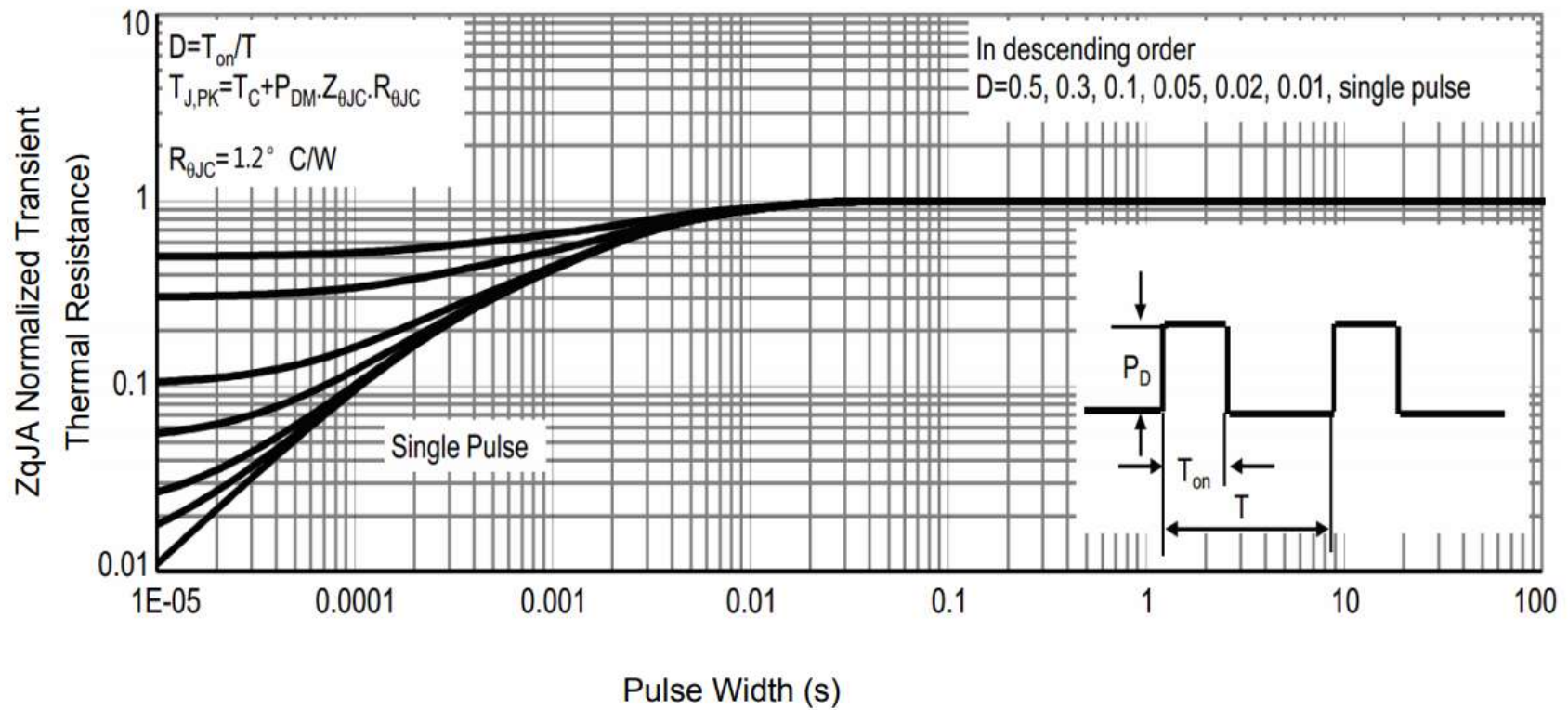
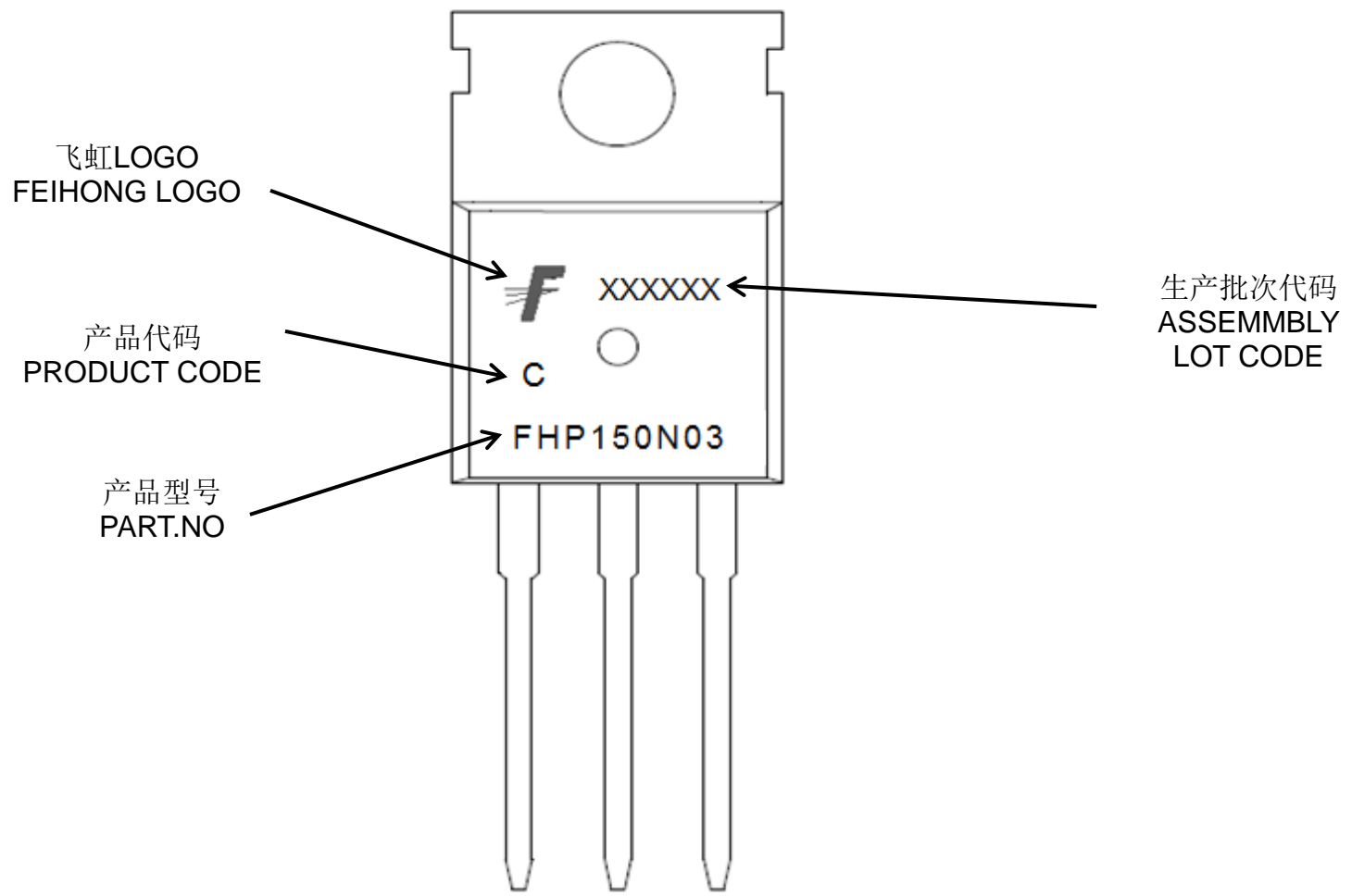


Fig9. Normalized Maximum Transient Thermal Impedance

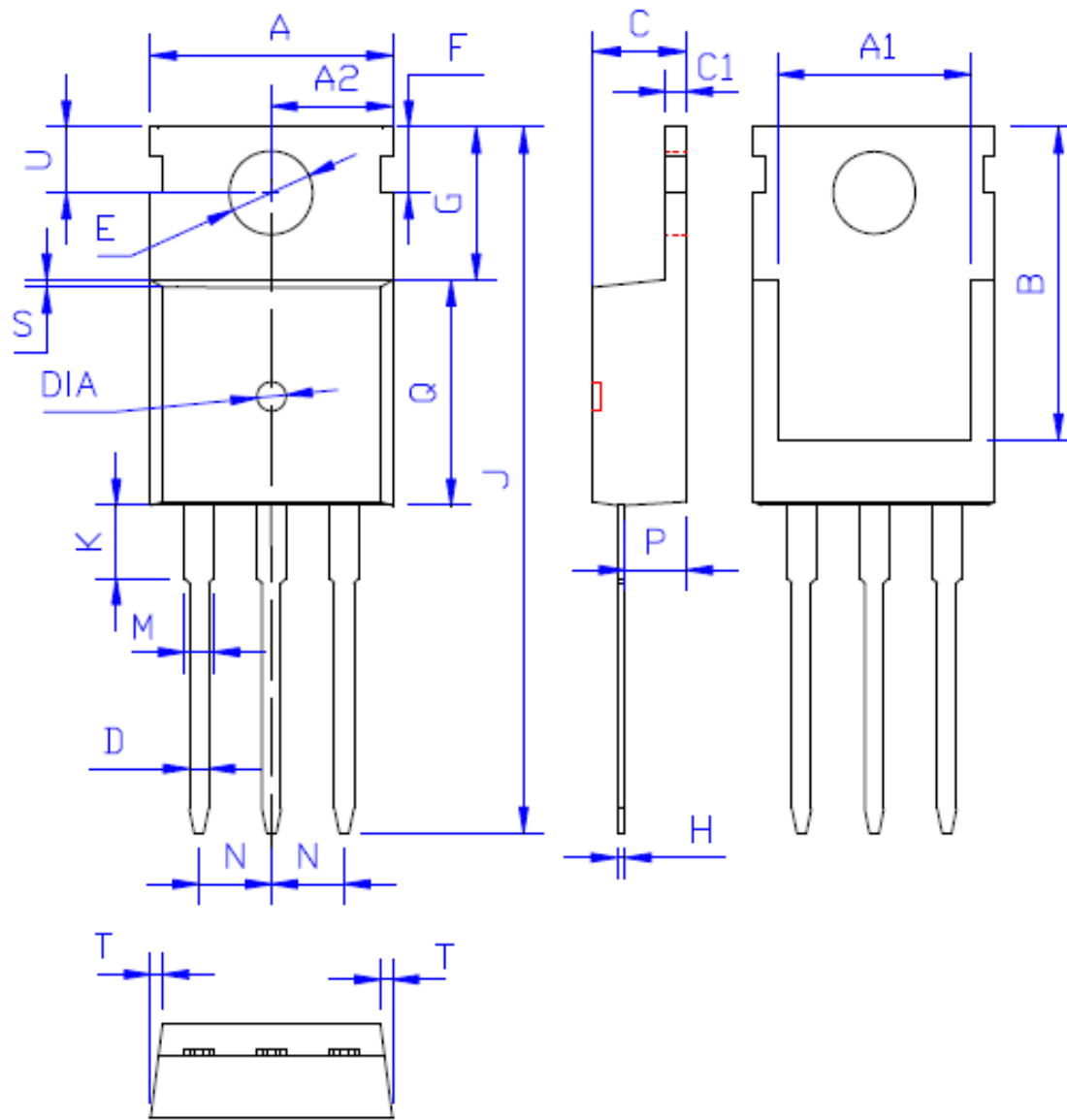
印记 Marking:



外形尺寸:

Package Dimension:

TO-220



DIM	MILLIMETERS
A	10.00 ± 0.30
A1	8.00 ± 0.30
A2	5.00 ± 0.30
B	13.20 ± 0.40
C	4.50 ± 0.20
C1	1.30 ± 0.20
D	0.80 ± 0.20
E	3.60 ± 0.20
F	3.00 ± 0.30
G	6.60 ± 0.40
H	0.50 ± 0.20
J	28.88 ± 0.50
K	3.00 ± 0.30
M	1.30 ± 0.30
N	Typical 2.54
P	2.40 ± 0.40
Q	9.20 ± 0.40
S	0.25 ± 0.15
T	0.25 ± 0.15
U	2.80 ± 0.30
DIA	宽 1.50 ± 0.10 深 0.50 MAX

(Unit: mm)